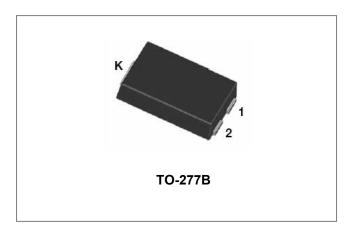


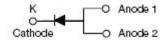




# ST12100S SCHOTTKY RECTIFIER



# Circuit Diagram



#### **Features**

- 150°C T<sub>J</sub> operation
- Low forward voltage drop
- High purity, high temperature epoxy encapsulation for enhanced mechanical strength and moisture resistance
- High frequency operation
- Guard ring for enhanced ruggedness and long term reliability
- Trench MOS Schottky technology
- "-A" is an AEC-Q101 qualified device
- This is a Pb Free Device
- All SMC parts are traceable to the wafer lot
- Additional testing can be offered upon request

#### **Applications**

- Switching power supply
- Converters
- Free-Wheeling diodes
- Reverse battery protection

### **Maximum Ratings:**

Characteristics	Symbol	Condition	Max.	Units
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V <sub>RRM</sub> V <sub>RWM</sub> V <sub>R</sub>	-	100	V
Average Rectified Forward Current	I <sub>F (AV)</sub>	50% duty cycle @T <sub>L</sub> =125°C, rectangular wave form	12	Α
Peak One Cycle Non-Repetitive Surge Current	I <sub>FSM</sub>	8.3ms, Half Sine pulse, T <sub>J</sub> = 25 °C	200	А

### **Electrical Characteristics:**

Characteristics	Symbol	Condition	Тур.	Max.	Units
Forward Voltage Drop*	$V_{F1}$	@ 5A, Pulse, T <sub>J</sub> = 25 °C @ 12A, Pulse, T <sub>J</sub> = 25 °C	0.50 0.68	- 0.70	V
	$V_{F2}$	@ 5A, Pulse, T <sub>J</sub> = 125 °C @ 12A, Pulse, T <sub>J</sub> = 125 °C	0.47 0.61	- 0.64	V
Reverse Current*	I <sub>R1</sub>	$@V_R = \text{rated } V_R$ $T_J = 25  ^{\circ}\text{C}$	0.02	0.3	mA
Reverse Current*	I <sub>R2</sub>	$@V_R = \text{rated } V_R$ $T_J = 125  ^{\circ}\text{C}$	28	50	mA
Junction Capacitance	Ст	$@V_R = 5V, T_C = 25 °C f_{SIG} = 1MHz$	600	-	pF

<sup>\*</sup> Pulse width < 300 µs, duty cycle < 2%

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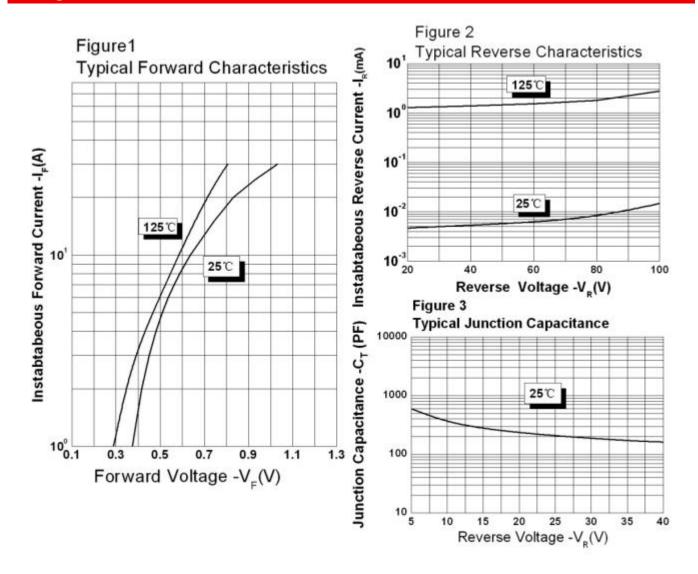


## **Thermal-Mechanical Specifications:**

Characteristics	Symbol	Condition	Specification	Units
Junction Temperature	TJ	-	-55 to +150	°C
Storage Temperature	T <sub>stg</sub>	-	-55 to +150	°C
Typical Thermal Resistance Junction to Ambient (NOTE1)	$R_{ heta JA}$	DC operation	75	°C/W
Typical Thermal Resistance Junction to Lead (NOTE1)	$R_{ hetaJL}$	DC operation	4	°C/W
Approximate Weight	wt	-	0.08	g

NOTE: 1. Units mounted on P.C.B., 0.5 x 0.5" (30 x 30mm) copper pads.

### **Ratings and Characteristics Curves**



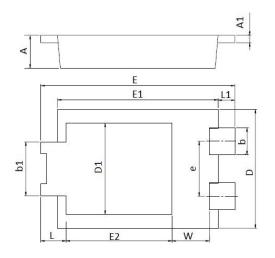
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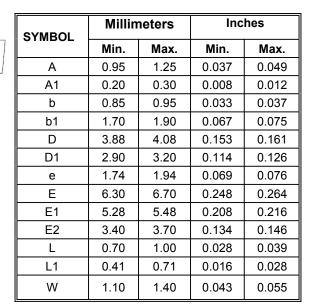




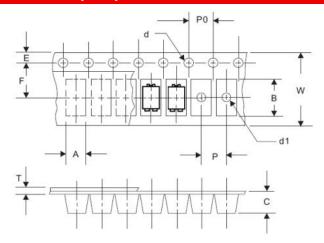


### **Mechanical Dimensions TO-277B**





## **Carrier Tape Specification TO-277B**



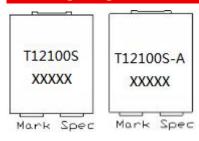
SYMBOL	Millim	eters
STIVIBUL	Min.	Max.
Α	4.28	4.48
В	6.80	7.10
С	1.30	1.50
d	1.40	1.60
d1	-	1.50
E	1.65	1.85
F	5.40	5.60
Р	7.90	8.10
P0	3.90	4.10
Т	0.24	0.44
W	11.70	12.30

## **Ordering Information**

Device	Package	Shipping		
ST12100S	TO-277B(Pb-Free)	5000pcs/ reel		

For information on tape and reel specifications, including part orientation and tape sizes, please refer to our tape and reel packaging specification.

#### **Marking Diagram**



Where XXXXX is YYWWL

= Device Type 12 = Forward Current (12A)

= Reverse Voltage (100V) 100 = Package type = AEC-Q101 S -A ΥY = Year WW = Week

Cautions: Molding resin

Epoxy resin UL:94V-0

= Lot Number

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